

THE SPECIFICATION OF AlGaAs IR LED CHIP "IP4J"

1. DESCRIPTION

This is a AlGaAs infrared LED chip. It is P-side up. The peak wavelength is 870 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (V_F) IF=20mA		1.4	1.6	V
Reverse Voltage (V_R) IR=10uA	5			V
Radiated Power ¹⁾ (P_o) IF=20mA	3.5			mW
Peak Wavelength (λ_p) IF=20mA	850	870	900	nm
Spectral Radiation Bandwidth ($\Delta\lambda$) IF=20mA		45		nm
Rise Time (T_r) IFp=100mA Tw=125ns,Duty=25%		20		ns
Fall Time (T_f) IFp=100mA Tw=125ns,Duty=25%		20		ns

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Continuous Maximum Forward Current	: 100 mA(DC)
Reverse Voltage	: 5 V(IR=10uA)
Storage Temperature	
while on mylar membrane	: 0 to 40 deg. C
after removal from mylar membrane	: -40 to 100 deg. C

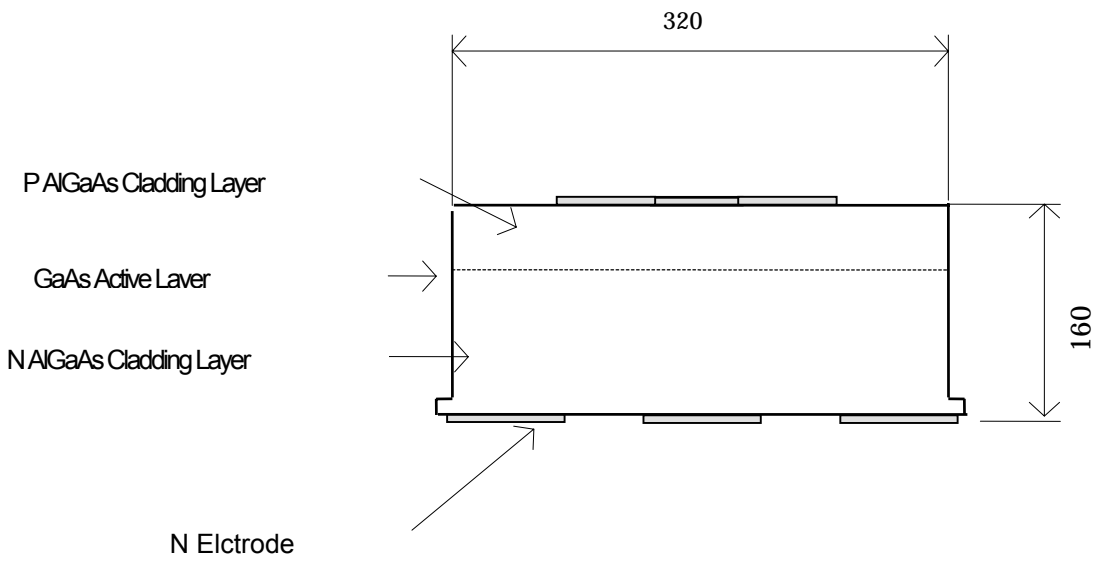
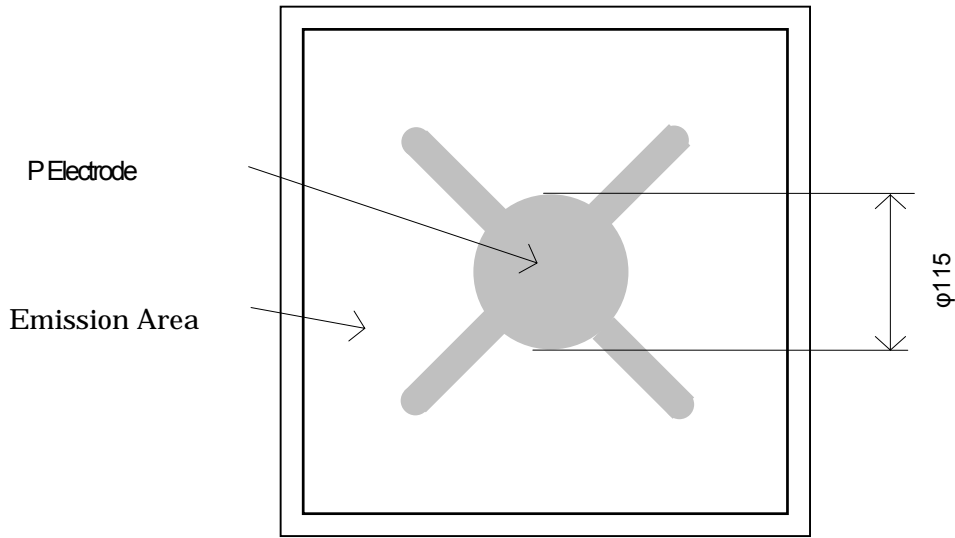
4. PHYSICAL CHARACTERISTICS AND STRUCTURE

1)Material	: AlGaAs
2)Structure	: Double Hetero Structure
3)Junction size	: 0.320mm × 0.320mm
4)Thickness	: 0.160mm
5)Bond Pad Size	: 0.115mm diameter
6)Anode Metallization	: Gold Alloy
7)Cathode Metallization	: Gold Alloy

6. Physical Dimensions

Model IP4J

UNIT:um



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.